CLAIMS

1. A sputtering target material, comprising, in at%, 35% to 50% of Ta with the balance being Ni and an inevitable impurity,

wherein the sputtering target material is composed only of a Ni_2Ta compound phase and a NiTa compound phase, and

wherein a microstructure in each of the Ni_2Ta compound phase and the NiTa compound phase has a maximum inscribed circle diameter of not more than 10 μm.